2SC4702

Silicon NPN Epitaxial

HITACHI

ADE-208-1120A (Z)
2nd. Edition
Mar. 2001

Application

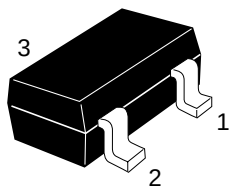
High voltage amplifier

Features

- High breakdown voltage
  V_{CEO} = 300 V
- Small Cob
  Cob = 1.5 pF Typ.

Outline

MPAK



1. Emitter
2. Base
3. Collector

Note: Marking is “XV–”.

Hitachi semiconductor

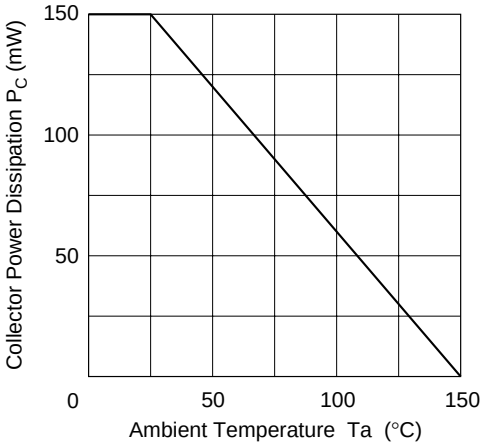
Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	300	V
Collector to emitter voltage	V_{CEO}	300	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

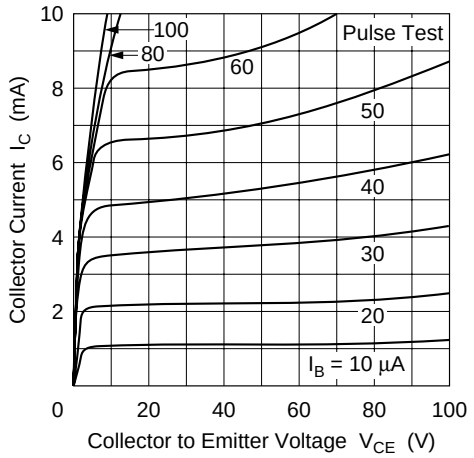
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	300	—	—	V	I_C = 10 µA, I_E = 0
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	300	—	—	V	I_C = 1 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	I_E = 10 µA, I_C = 0
Collector cutoff current	I_{CBO}	—	—	0.1	µA	V_{CB} = 250 V, I_E = 0
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.5	V	I_C = 30 mA, I_B = 3 mA
DC current transfer ratio	h_{FE}	60	—	150		V_{CE} = 6 V, I_C = 2 mA
Gain bandwidth product	f_T	—	80	—	MHz	V_{CE} = 6 V, I_C = 5 mA
Collector output capacitance	Cob	—	1.5	—	pF	V_{CB} = 10 V, I_E = 0, f = 1 MHz

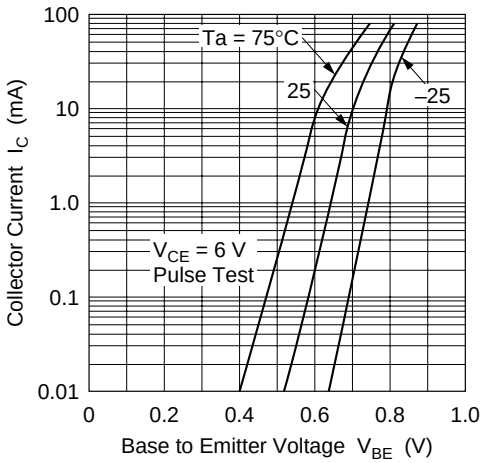
Maximum Collector Dissipation Curve



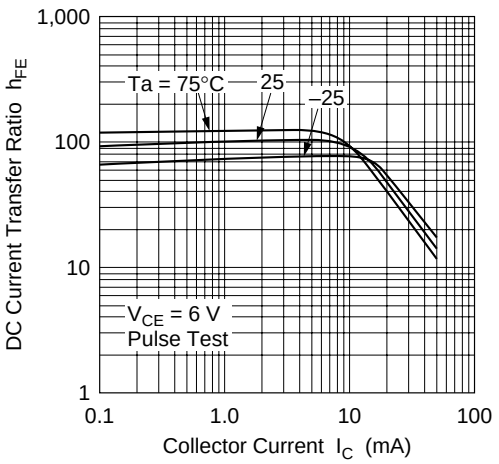
Typical Output Characteristics



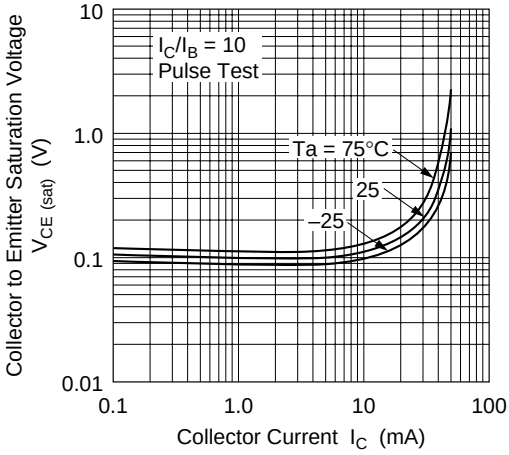
Typical Transfer Characteristics



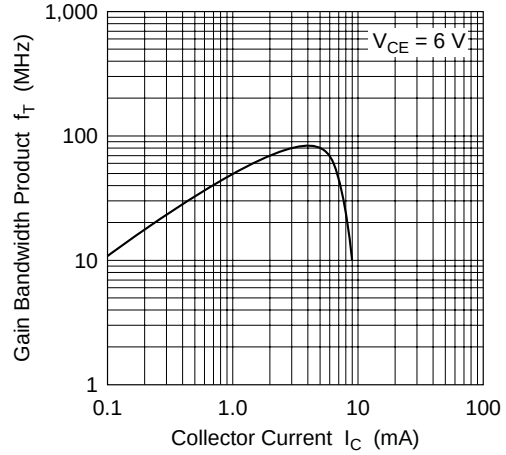
DC Current Transfer Ratio vs. Collector Current



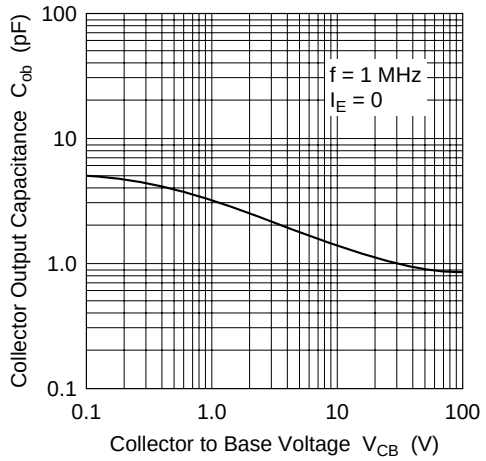
Collector to Emitter Saturation Voltage vs. Collector Current



Gain Bandwidth Product vs. Collector Current

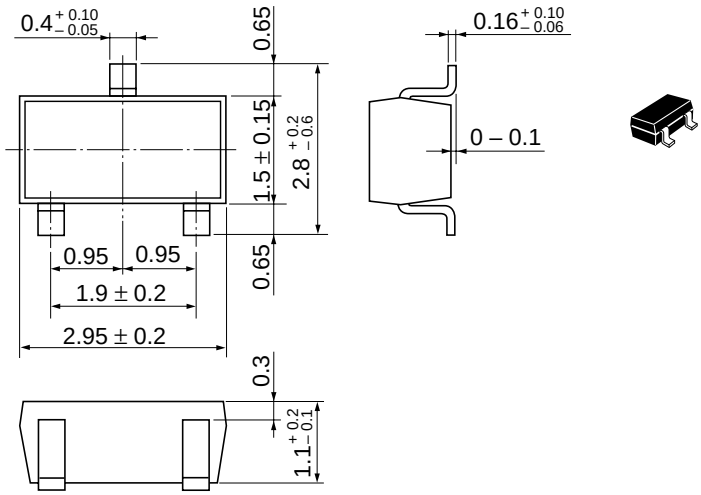


Collector Output Capacitance vs. Collector to Base Voltage



Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	MPAK
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.011 g

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